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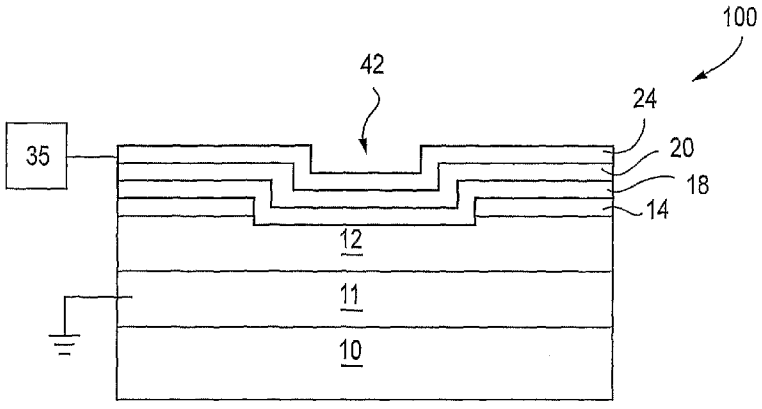
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(54) Title: PHASE CHANGE MEMORY CELL AND METHOD OF FORMATION



(57) Abstract: A phase change memory element and methods for forming the same are provided. The memory element includes a first electrode (12) and a chalcogenide comprising phase change material layer (18) over the first electrode. A metal -chalcogenide layer (20) is over the phase change material layer. The metal chalcogenide layer is tin- telluride. A second electrode (24) is over the metal-chalcogenide layer. The memory element is configured to have reduced current requirements .

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